Description

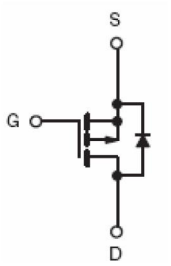
The **VS10P03-S8** uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a load switch or in PWM applications.

General Features

- V_{DS} = -30V,I_D = -10A
  $R_{DS(ON)}$ < 34mΩ @ V_{GS}=-4.5V
  $R_{DS(ON)}$ < 21mΩ @ V_{GS}=-10V
- High Power and current handing capability
- Lead free product is acquired
- Surface mount package

Application

- PWM applications
- Load switch
- Power management



Schematic diagram

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
VS10P03-S8	**VS10P03-S8**	SOP-8	Ø330mm	12mm	

Absolute Maximum Ratings (T_A=25℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	-30	V
Gate-Source Voltage	V_{GS}	±20	V
Drain Current-Continuous (T_C=25℃)	I_D	-10	A
Drain Current-Continuous (T_C=100℃)		-7.1	
Drain Current-Pulsed (Note 1)	I_{DM}	-40	A
Maximum Power Dissipation (T_C=25℃)	P_D	3	W
Maximum Power Dissipation (T_C=100℃)		1.3	
Single pulse avalanche energy (Note 5)	E_{AS}	231	mJ
Operating Junction and Storage Temperature Range	T_J,T_{STG}	-55 To 150	℃

Thermal Characteristic

Thermal Resistance,Junction-to-Ambient (Note 2)	$R_{\theta JA}$	41.67	℃/W

Electrical Characteristics (T_A=25℃unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V I_D=-250μA	-30	-33	-	V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=-30V,V_{GS}=0V	-	-	-1	μA
Gate-Body Leakage Current	I_{GSS}	V_{GS}=±20V,V_{DS}=0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS},I_D=-250μA	-1	-1.6	-2.2	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	V_{GS}=-10V, I_D=-10A	-	17.6	21	mΩ
		V_{GS}=-4.5V, I_D=-10A	-	25.5	34	mΩ
Forward Transconductance	g_{FS}	V_{DS}=-5V,I_D=-10A	-	20	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C_{lss}	V_{DS}=-15V,V_{GS}=0V, F=1.0MHz	-	1253	-	PF
Output Capacitance	C_{oss}		-	181	-	PF
Reverse Transfer Capacitance	C_{rss}		-	158	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	$t_{d(on)}$	V_{DD}=-15V, ID=-10A, V_{GS}=-10V,R_{GEN}=1Ω	-	8	-	nS
Turn-on Rise Time	t_r		-	9	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	26	-	nS
Turn-Off Fall Time	t_f		-	8	-	nS
Total Gate Charge	Q_g	V_{DS}=-15V,I_D=-10A,V_{GS}=-10V	-	24.4	-	nC
Gate-Source Charge	Q_{gs}		-	3.2	-	nC
Gate-Drain Charge	Q_{gd}		-	6.4	-	nC
Drain-Source Diode Characteristics						
Diode Forward Current (Note 2)	I_S		-	-	-10	A
Diode Forward Voltage (Note 3)	V_{SD}	V_{GS}=0V,I_S=-10A	-	-	-1.2	V

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, t ≤ 10 sec.
3. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
4. Guaranteed by design, not subject to production
5. E_{AS} condition: Tj=25℃,V_{DD}=-15V,V_G=10V,L=0.5mH,Rg=25Ω

Typical Electrical and Thermal Characteristics

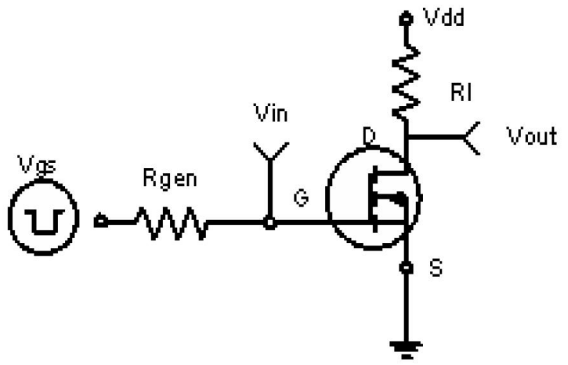


Figure 1:Switching Test Circuit

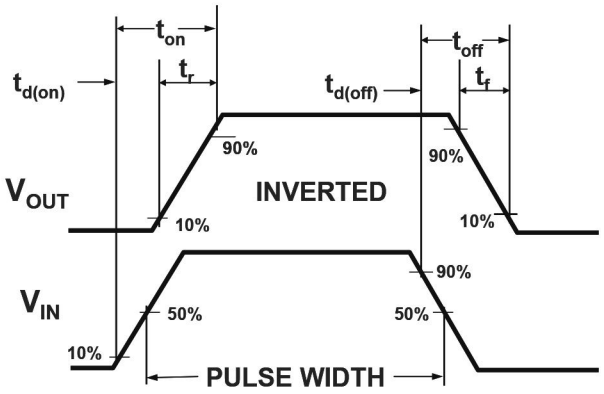


Figure 2:Switching Waveforms

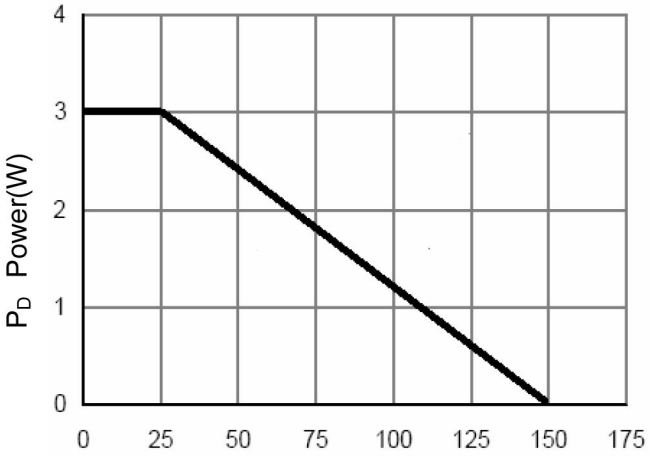


Figure 3 Power Dissipation

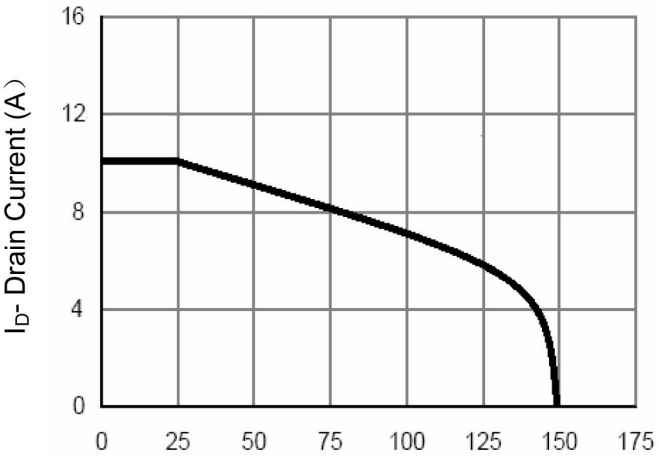


Figure 4 Drain Current

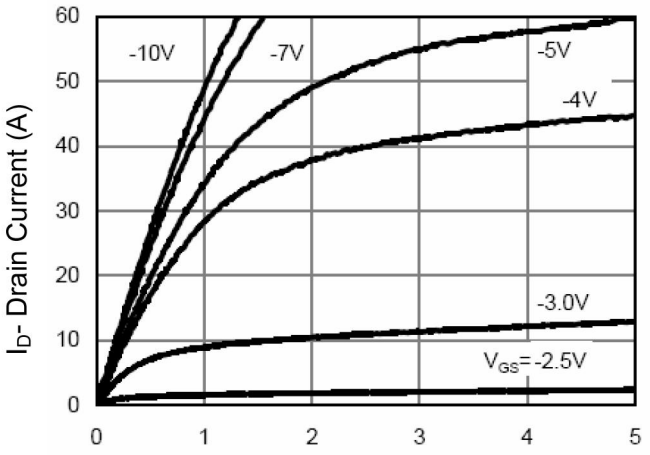


Figure 5 Output Characteristics

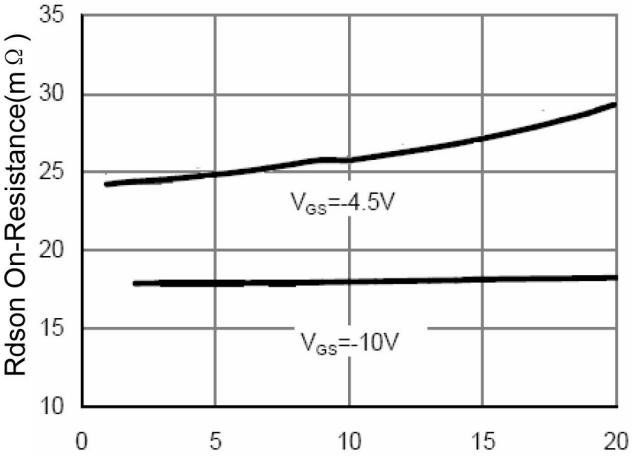


Figure 6 Drain-Source On-Resistance

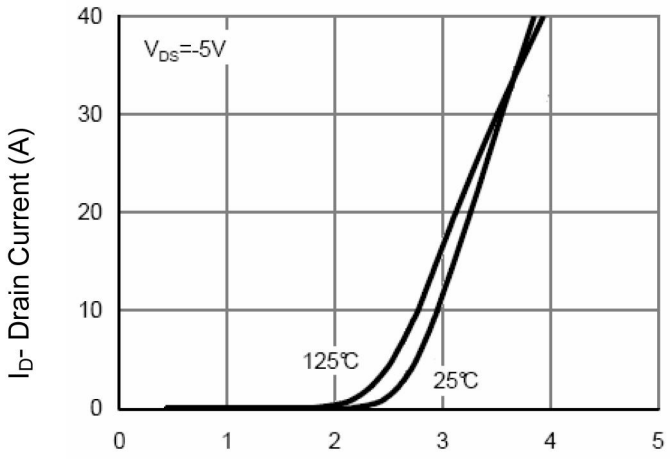


Figure 7 Transfer Characteristics

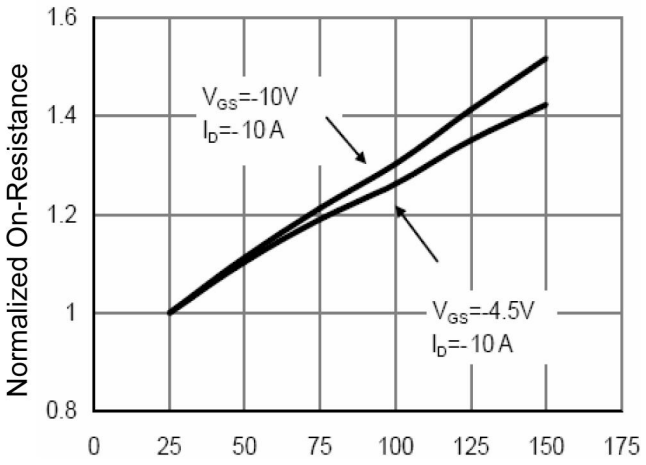


Figure 8 Drain-Source On-Resistance

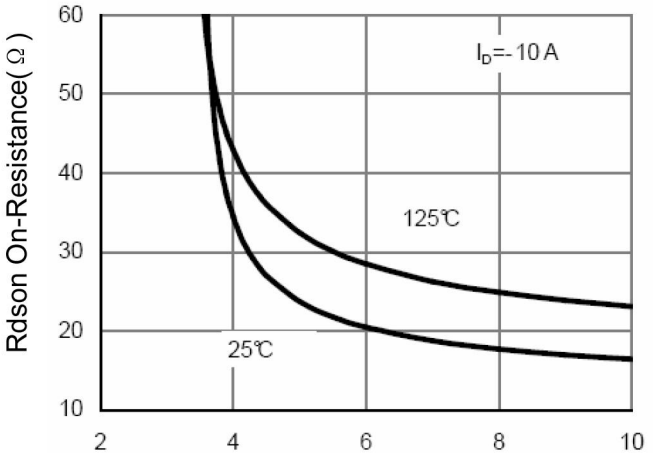


Figure 9 Rdson vs Vgs

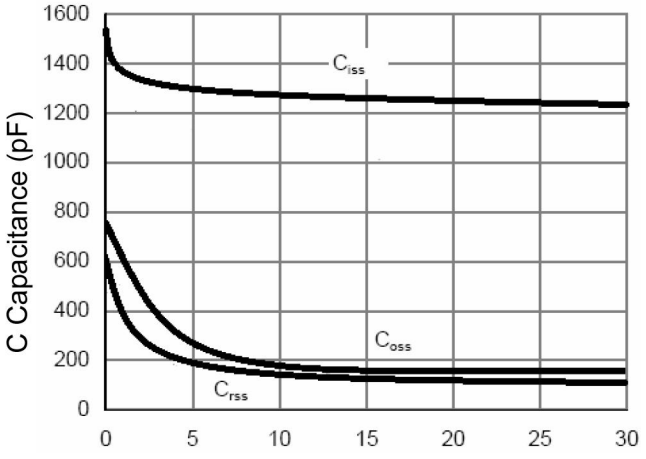


Figure 10 Capacitance vs Vds

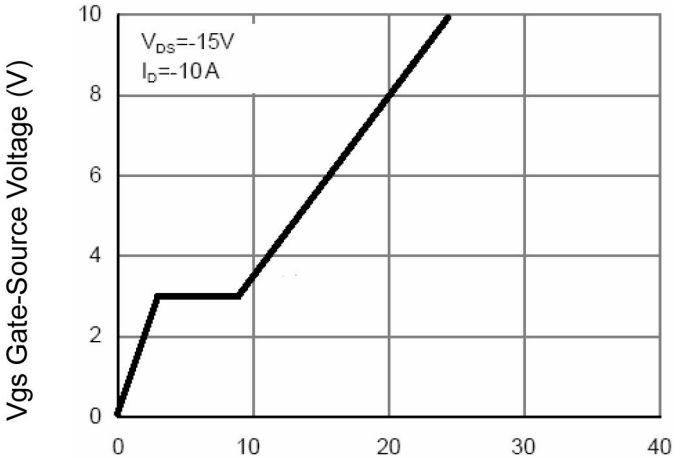


Figure 11 Gate Charge

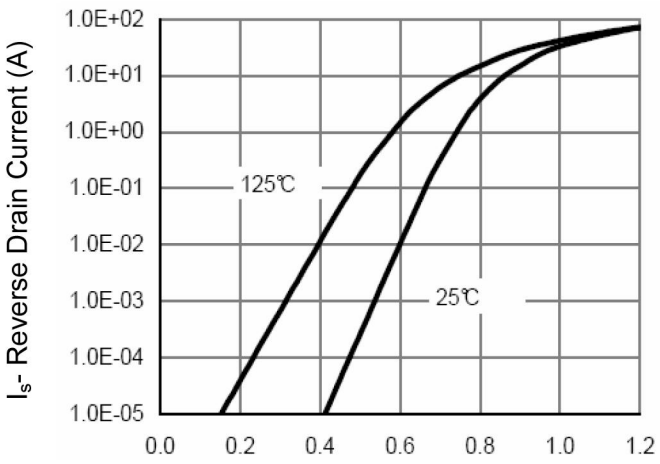


Figure 12 Source- Drain Diode Forward

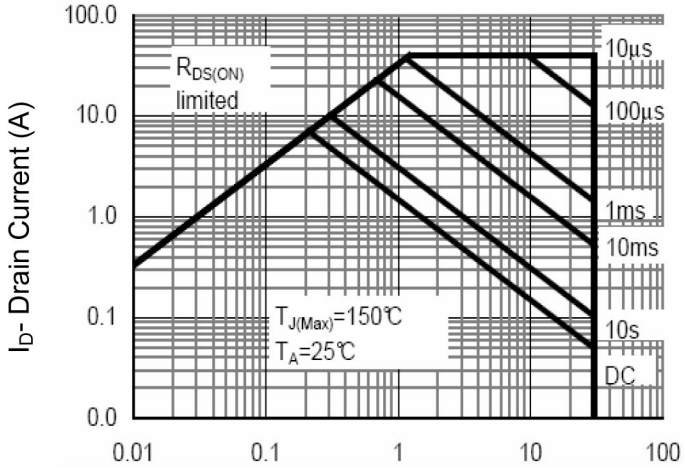


Figure 13 Safe Operation Area

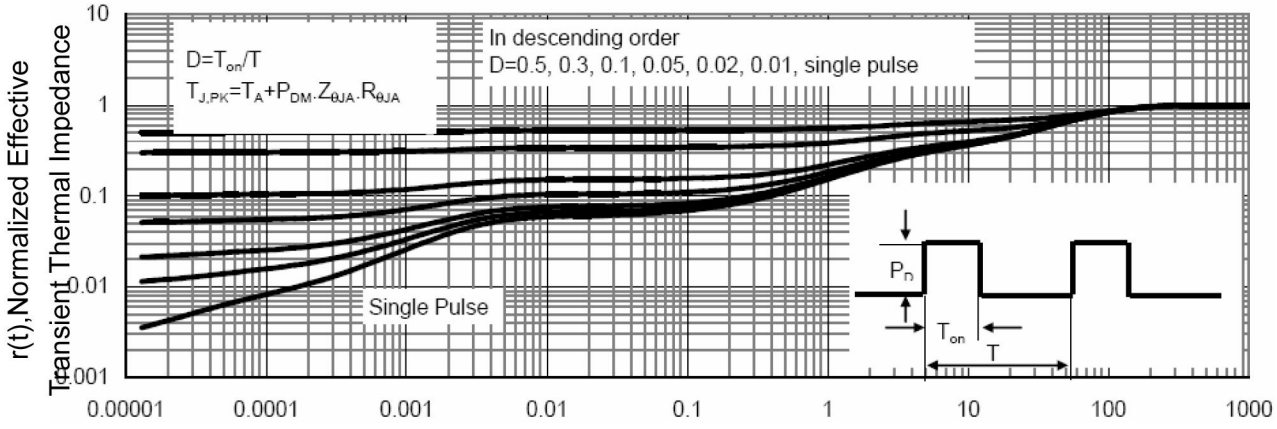


Figure 14 Normalized Maximum Transient Thermal Impedance